INTERCONNECT STRUCTURE AND METHOD FOR ITS FABRICATING

ABSTRACT

[0035] A method of fabricating an interconnect structure, including providing a semiconductor substrate having a first conductive layer thereon, and forming a dielectric layer overlying the semiconductor substrate and the first conductive layer. An opening is formed in the dielectric layer extending to the first conductive layer. A portion of the first conductive layer is removed through the opening to form a recess having a substantially curvilinear profile. The opening and the recess are filled with a second conductive layer.

(FIG. 1)